

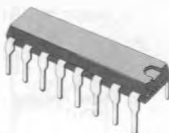
5W AUDIO AMPLIFIER WITH MUTING

The TDA1905 is a monolithic integrated circuit in POWERDIP package, intended for use as low frequency power amplifier in a wide range of applications in radio and TV sets:

- muting facility
- protection against chip over temperature
- very low noise
- high supply voltage rejection
- low "switch-on" noise
- voltage range 4V to 30V

The TDA 1905 is assembled in a new plastic package, the POWERDIP, that offers the same

assembly ease, space and cost saving of a normal dual in-line package but with a power dissipation of up to 6W and a thermal resistance of 15°C/W (junction to pins).



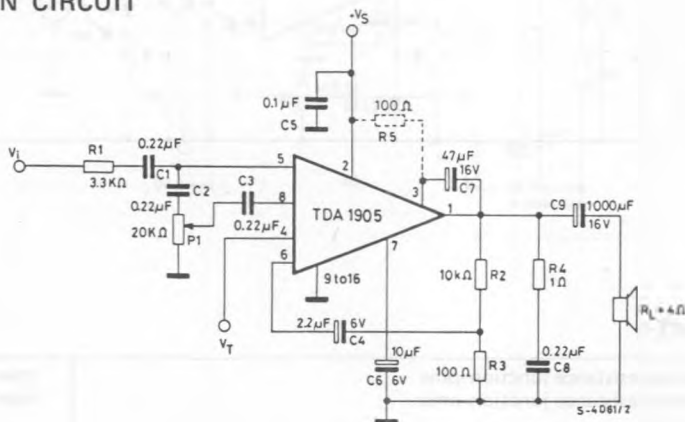
Powerdip
(8 + 8)

ORDERING NUMBER: TDA1905

ABSOLUTE MAXIMUM RATINGS

V_s	Supply voltage	30	V
I_o	Output peak current (non repetitive)	3	A
I_o	Output peak current (repetitive)	2.5	A
V_i	Input voltage	0 to $+V_s$	V
V_i	Differential input voltage	± 7	V
V_{11}	Muting threshold voltage	V_s	V
P_{tot}	Power dissipation at $T_{amb} = 80^{\circ}\text{C}$ $T_{case} = 60^{\circ}\text{C}$	1	W
		6	W
T_{stg}, T_j	Storage and junction temperature	-40 to 150	$^{\circ}\text{C}$

APPLICATION CIRCUIT

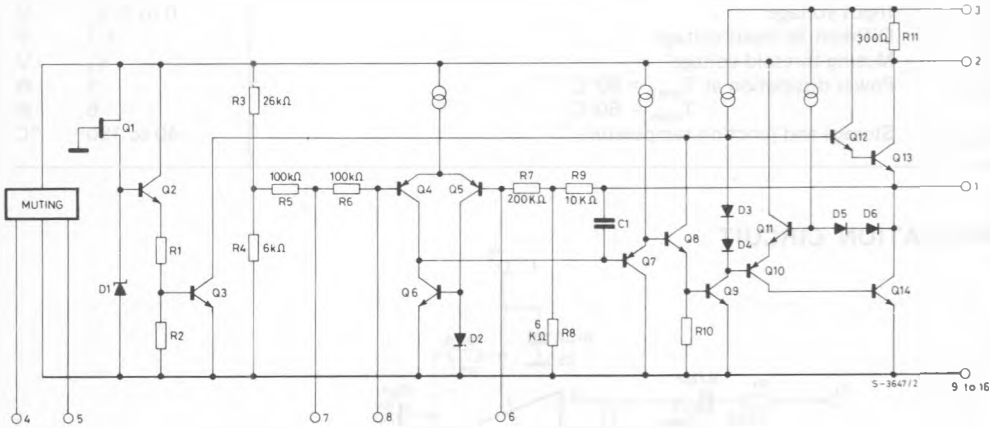


CONNECTION DIAGRAM

(Top view)



SCHEMATIC DIAGRAM

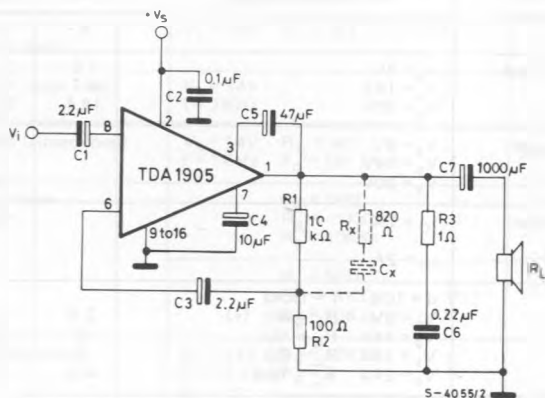


THERMAL DATA

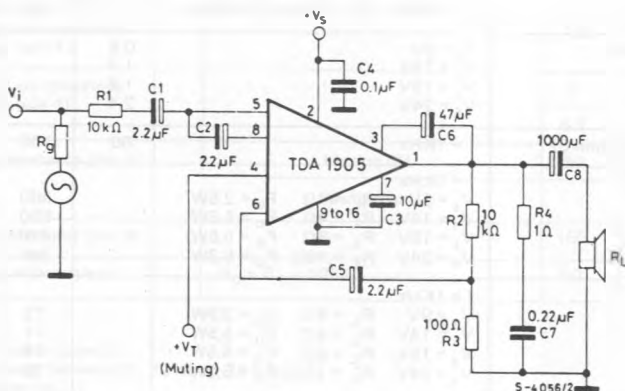
$R_{thj-case}$	Thermal resistance junction-pins	max	15 °C/W
$R_{thj-amb}$	Thermal resistance junction-amb	max	70 °C/W

TEST CIRCUITS:

WITHOUT MUTING



WITH MUTING FUNCTION



ELECTRICAL CHARACTERISTICS (Refer to the test circuit, $T_{amb} = 25^{\circ}\text{C}$, R_{th} (heatsink) = 20°C/W , unless otherwise specified)

Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_s Supply voltage		4		30	V
V_o Quiescent output voltage	$V_s = 4\text{V}$ $V_s = 14\text{V}$ $V_s = 30\text{V}$	1.6 6.7 14.4	2.1 7.2 15.5	2.5 7.8 16.8	V
I_d Quiescent drain current	$V_s = 4\text{V}$ $V_s = 14\text{V}$ $V_s = 30\text{V}$		15 17 21	35	mA
$V_{CE\text{ sat}}$ Output stage saturation voltage	$I_C = 1\text{A}$ $I_C = 2\text{A}$		0.5 1		V
P_o Output power	$d = 10\%$ $f = 1\text{KHz}$ $V_s = 9\text{V}$ $R_L = 4\Omega$ (*) $V_s = 14\text{V}$ $R_L = 4\Omega$ $V_s = 18\text{V}$ $R_L = 8\Omega$ $V_s = 24\text{V}$ $R_L = 16\Omega$	2.2 5 5 4.5	2.5 5.5 5.5 5.3		W
d Harmonic distortion	$f = 1\text{KHz}$ $V_s = 9\text{V}$ $R_L = 4\Omega$ $P_o = 50\text{ mW to } 1.5\text{W}$ $V_s = 14\text{V}$ $R_L = 4\Omega$ $P_o = 50\text{ mW to } 3\text{W}$ $V_s = 18\text{V}$ $R_L = 8\Omega$ $P_o = 50\text{ mW to } 3\text{W}$ $V_s = 24\text{V}$ $R_L = 16\Omega$ $P_o = 50\text{ mW to } 3\text{W}$		0.1 0.1 0.1 0.1		%
V_i Input sensitivity	$f = 1\text{KHz}$ $V_s = 9\text{V}$ $R_L = 4\Omega$ $P_o = 2.5\text{W}$ $V_s = 14\text{V}$ $R_L = 4\Omega$ $P_o = 5.5\text{W}$ $V_s = 18\text{V}$ $R_L = 8\Omega$ $P_o = 5.5\text{W}$ $V_s = 24\text{V}$ $R_L = 16\Omega$ $P_o = 5.3\text{W}$		37 49 73 100		mV
V_i Input saturation voltage (rms)	$V_s = 9\text{V}$ $V_s = 14\text{V}$ $V_s = 18\text{V}$ $V_s = 24\text{V}$	0.8 1.3 1.8 2.4			V
R_i Input resistance (pin 8)	$f = 1\text{KHz}$	60	100		$\text{K}\Omega$
I_d Drain current	$f = 1\text{KHz}$ $V_s = 9\text{V}$ $R_L = 4\Omega$ $P_o = 2.5\text{W}$ $V_s = 14\text{V}$ $R_L = 4\Omega$ $P_o = 5.5\text{W}$ $V_s = 18\text{V}$ $R_L = 8\Omega$ $P_o = 5.5\text{W}$ $V_s = 24\text{V}$ $R_L = 16\Omega$ $P_o = 5.3\text{W}$		380 550 410 295		mA
η Efficiency	$f = 1\text{KHz}$ $V_s = 9\text{V}$ $R_L = 4\Omega$ $P_o = 2.5\text{W}$ $V_s = 14\text{V}$ $R_L = 4\Omega$ $P_o = 5.5\text{W}$ $V_s = 18\text{V}$ $R_L = 8\Omega$ $P_o = 5.5\text{W}$ $V_s = 24\text{V}$ $R_L = 16\Omega$ $P_o = 5.3\text{W}$		73 71 74 75		%

(*) With an external resistor of 100Ω between pin 3 and $+V_s$.

ELECTRICAL CHARACTERISTICS (continued)

Parameter	Test conditions	Min.	Typ.	Max.	Unit
BW	Small signal bandwidth (-3dB) $V_s = 14V$ $R_L = 4\Omega$ $P_O = 1W$	40 to 40,000			Hz
G_v	Voltage gain (open loop) $V_s = 14V$ $f = 1KHz$		75		dB
G_v	Voltage gain (closed loop) $V_s = 14V$ $R_L = 4\Omega$ $f = 1KHz$ $P_O = 1W$	39.5	40	40.5	dB
e_N	Total input noise $R_g = 50\Omega$ $R_g = 1K\Omega$ $R_g = 10K\Omega$ $(^{\circ})$		1.2 1.3 1.5	4.0	μV
			2.0 2.0 2.2	6.0	μV
S/N	Signal to noise ratio $V_s = 14V$ $R_g = 10K\Omega$ $P_O = 5.5W$ $R_g = 0$ $(^{\circ})$ $R_L = 4\Omega$		90 92		dB
			87 87		dB
SVR	Supply voltage rejection $V_s = 18V$ $R_L = 8\Omega$ $f_{ripple} = 100 Hz$ $R_g = 10K\Omega$ $V_{ripple} = 0.5V_{rms}$	40	50		dB
T_{sd}	Thermal shut-down case temperature $(^{\circ})$ $P_{tot} = 2.5W$		115		$^{\circ}C$

MUTING FUNCTION

V_{TOFF}	Muting-off threshold voltage (pin 4)	1.9		4.7	V
V_{TON}	Muting-on threshold voltage (pin 4)	0		1.3	V
		6.2		V_s	
R_5	Input resistance (pin 5)	Muting off	80	200	$K\Omega$
		Muting on		10	Ω
R_4	Input resistance (pin 4)	150			$K\Omega$
A_T	Muting attenuation $R_g + R_1 = 10K\Omega$	50	60		dB

Note:

- $(^{\circ})$ Weighting filter = curve A.
 $(^{\circ\circ})$ Filter with noise bandwidth: 22 Hz to 22 KHz.
 $(^{\circ})$ See fig. 30 and fig. 31

Fig. 1 - Quiescent output voltage vs. supply voltage

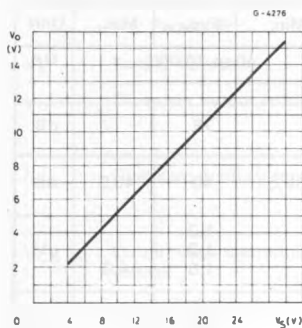


Fig. 2 - Quiescent drain current vs. supply voltage

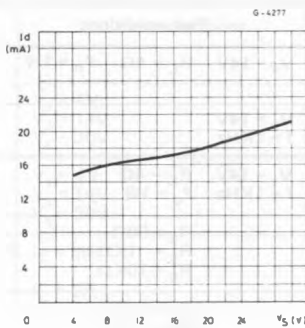


Fig. 3 - Output power vs. supply voltage

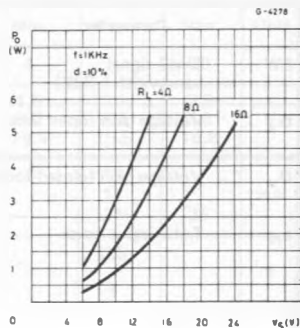
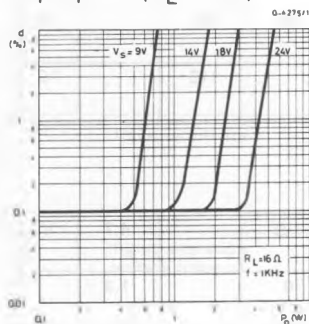
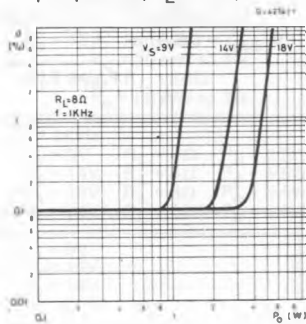
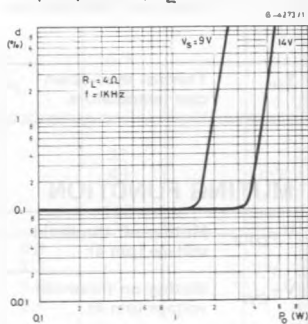
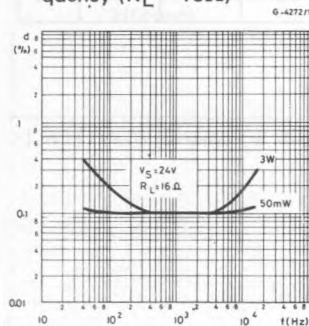
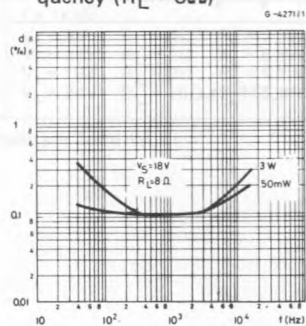
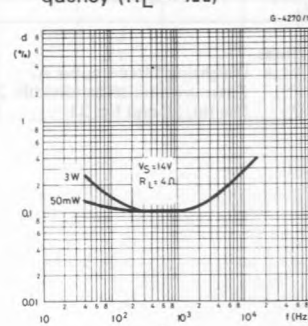
Fig. 4 - Distortion vs. output power ($R_L = 16\Omega$)Fig. 5 - Distortion vs. output power ($R_L = 8\Omega$)Fig. 6 - Distortion vs. output power ($R_L = 4\Omega$)Fig. 7 - Distortion vs. frequency ($R_L = 16\Omega$)Fig. 8 - Distortion vs. frequency ($R_L = 8\Omega$)Fig. 9 - Distortion vs. frequency ($R_L = 4\Omega$)

Fig. 10 - Open loop frequency response

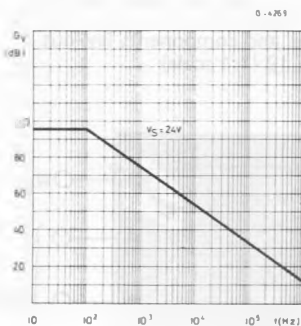


Fig. 11 - Output power vs. input voltage

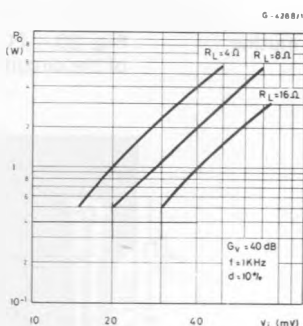
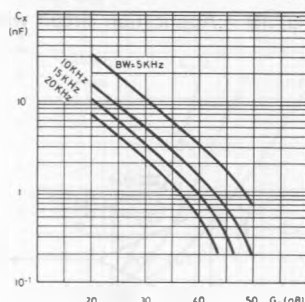
Fig. 12 - Value of capacitor C_x vs. bandwidth (BW) and gain (G_v)

Fig. 13 - Supply voltage rejection vs. voltage gain (ref. to the Muting circuit)

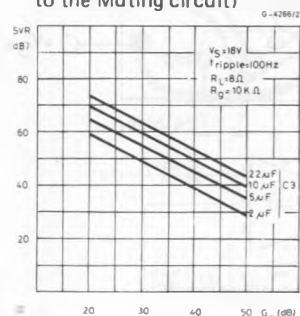


Fig. 14 - Supply voltage rejection vs. source resistance

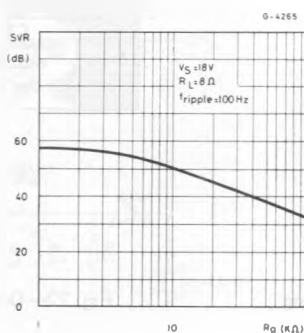


Fig. 15 - Max power dissipation vs. supply voltage (sine wave operation)

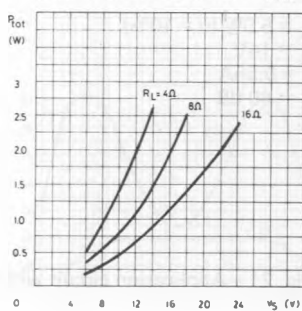


Fig. 16 - Power dissipation and efficiency vs. output power

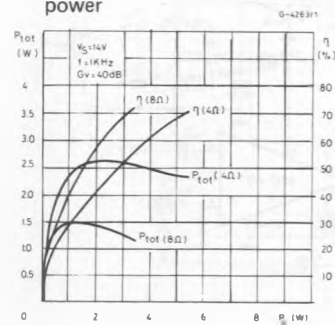


Fig. 17 - Power dissipation and efficiency vs. output power

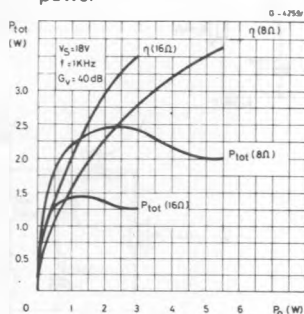
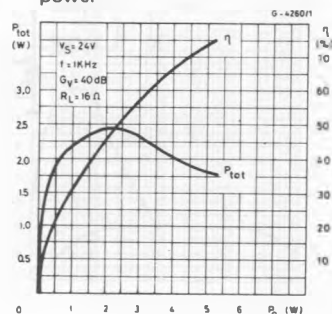
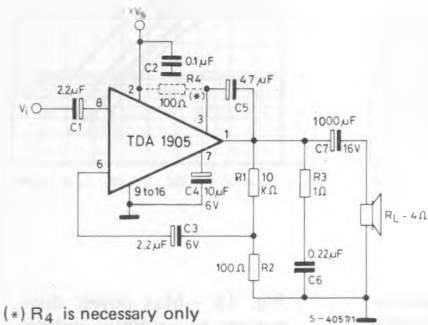


Fig. 18 - Power dissipation and efficiency vs. output power



APPLICATION INFORMATION

Fig. 19 – Application circuit without muting



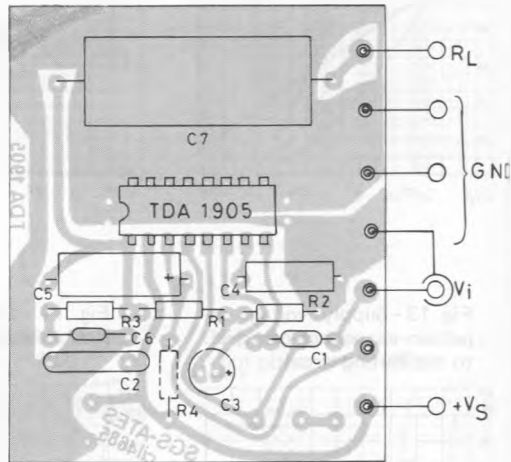
$P_o = 5.5W$ ($d = 10\%$)

$V_S = 14V$

$I_d = 0.55A$

$G_v = 40\text{ dB}$

Fig. 20 – PC board and components lay-out of the circuit of Fig. 19 (1:1 scale)



CS-0129/1

Fig. 21 – Application circuit with muting

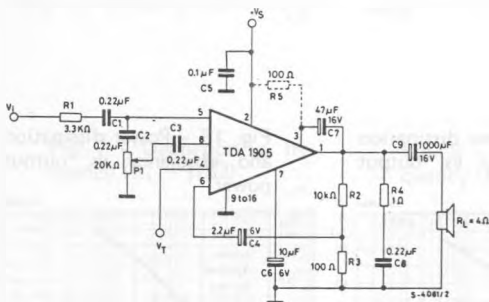
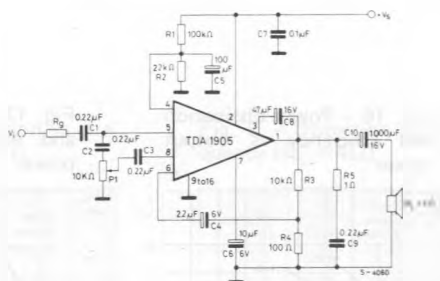


Fig. 22 – Delayed muting circuit



APPLICATION INFORMATION (continued)

Fig. 23 – Low-cost application circuit without bootstrap.

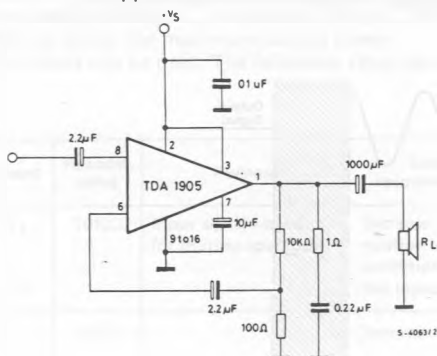


Fig. 25 – Two position DC tone control using change of pin 5 resistance (muting function)

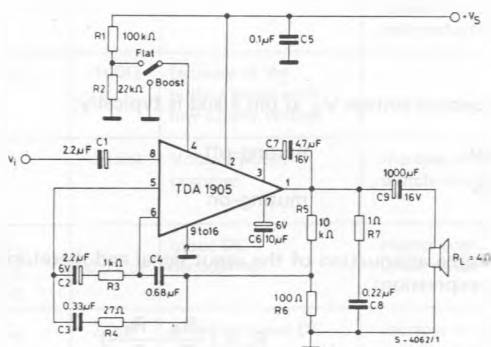


Fig. 27 – Bass Bomb tone control using change of pin 5 resistance (muting function)

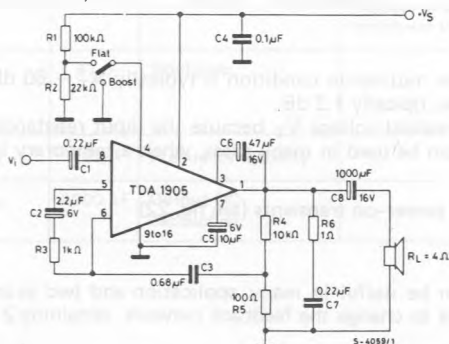


Fig. 24 – Output power vs. supply voltage (circuit of fig. 23)

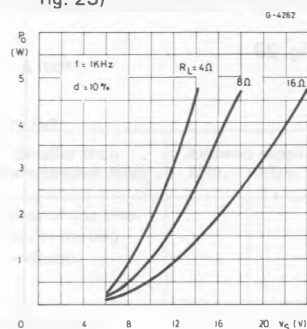


Fig. 26 – Frequency response of the circuit of fig. 25

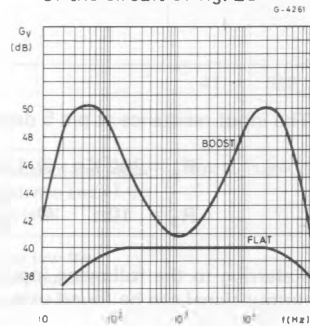
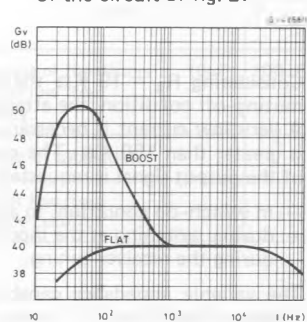


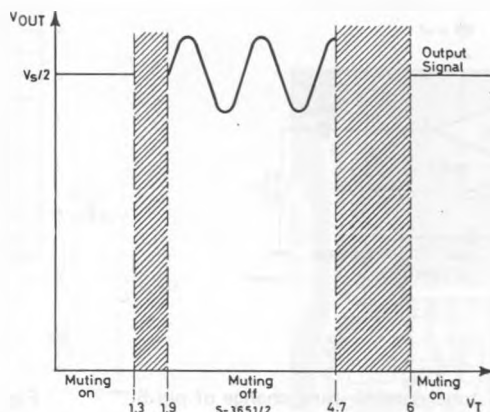
Fig. 28 – Frequency response of the circuit of fig. 27



MUTING FUNCTION

The output signal can be inhibited applying a DC voltage V_T to pin 4, as shown in fig. 29

Fig. 29

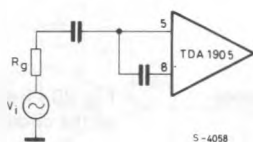


The input resistance at pin 5 depends on the threshold voltage V_T at pin 4 and is typically:

$$R_5 = 200 \text{ K}\Omega \quad @ \quad 1.9\text{V} \leq V_T \leq 4.7\text{V} \quad \text{muting-off}$$

$$R_5 = 10\Omega \quad @ \quad \begin{array}{l} 0\text{V} \leq V_T \leq 1.3\text{V} \\ 6\text{V} \leq V_T \leq V_S \end{array} \quad \text{muting-on}$$

Referring to the following input stage, the possible attenuation of the input signal and therefore of the output signal can be found using the following expression:



$$A_T = \frac{V_i}{V_8} = \frac{R_g + \left(\frac{R_8 \cdot R_5}{R_8 + 5} \right)}{\left(\frac{R_8 \cdot R_5}{R_8 + R_5} \right)}$$

$$\text{where } R_8 \cong 100 \text{ K}\Omega$$

Considering $R_g = 10 \text{ K}\Omega$ the attenuation in the muting-on condition is typically $A_T = 60 \text{ dB}$. In the muting-off condition, the attenuation is very low, typically 1.2 dB .

A very low current is necessary to drive the threshold voltage V_T because the input resistance at pin 4 is greater than $150 \text{ K}\Omega$. The muting function can be used in many cases, when a temporary inhibition of the output signal is requested, for example:

- in switch-on condition, to avoid preamplifier power-on transients (see fig. 22)
- during switching at the input stages.
- during the receiver tuning.

The variable impedance capability at pin 5 can be useful in many application and two examples are shown in fig. 25 and 27, where it has been used to change the feedback network, obtaining 2 different frequency response.

APPLICATION SUGGESTION

The recommended values of the external components are those shown on the application circuit of fig. 21. When the supply voltage V_s is less than 10V, a 100 Ω resistor must be connected between pin 2 and pin 3 in order to obtain the maximum output power.

Different values can be used. The following table can help the designer.

Component	Raccom. value	Purpose	Larger than recommended value	Smaller than recommended value	Allowed range	
					Min.	Max.
$R_9 + R_1$	10K Ω	Input signal impeded for muting operation	Increase of the attenuation in muting-on condition. Decrease of the input sensitivity.	Decrease of the attenuation in muting-on condition.		
R_2	10K Ω	Feedback resistors	Increase of gain.	Decrease of gain. Increase quiescent current.	$9 R_3$	
R_3	100 Ω		Decrease of gain.	Increase of gain.		1K Ω
R_4	1 Ω	Frequency stability	Danger of oscillation at high frequencies with inductive loads.			
R_5	100 Ω	Increase of the output swing with low supply voltage.			47	330
P_1	20K Ω	Volume potentiometer	Increase of the switch-on noise.	Decrease of the input impedance and of the input level.	10K Ω	100K Ω
C_1 C_2 C_3	0.22 μ F	Input DC decoupling.	Higher cost lower noise.	Higher low frequency cutoff. Higher noise		
C_4	2.2 μ F	Inverting input DC decoupling.	Increase of the switch-on noise.	Higher low frequency cutoff.	0.1 μ F	
C_5	0.1 μ F	Supply voltage bypass.		Danger of oscillations.		
C_6	10 μ F	Ripple rejection	Increase of SVR increase of the switch-on time	Degradation of SVR	2.2 μ F	100 μ F
C_7	47 μ F	Bootstrap.		Increase of the distortion at low frequency.	10 μ F	100 μ F
C_8	0.22 μ F	Frequency stability.		Danger of oscillation.		
C_9	1000 μ F	Output DC decoupling.		Higher low frequency cutoff.		

THERMAL SHUT-DOWN

The presence of a thermal limiting circuit offers the following advantages:

- 1) An overload on the output (even if it is permanent), or an above limit ambient temperature can be easily tolerated since the T_j cannot be higher than 150°C .
- 2) The heatsink can have a smaller factor of safety compared with that of a conventional circuit. There is no possibility of device damage due to high junction temperature.
If for any reason, the junction temperature increases up to 150°C , the thermal shut-down simply reduces the power dissipation and the current consumption.

The maximum allowable power dissipation depends upon the size of the external heatsink (i.e. its thermal resistance); fig. 32 shows this dissippable power as a function of ambient temperature for different thermal resistance.

Fig. 30 - Output power and drain current vs. case temperature.

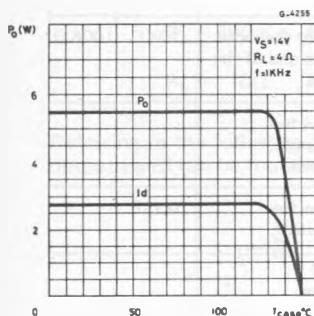


Fig. 31 - Output power and drain current vs. case temperature

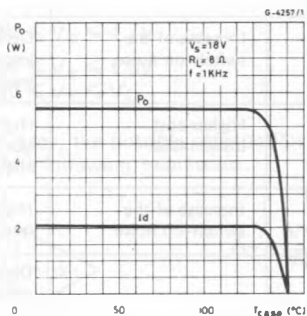
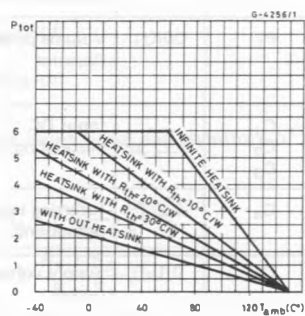


Fig. 32 - Maximum allowable power dissipation vs. ambient temperature.



MOUNTING INSTRUCTION: See TDA1904